

TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (π -MOSIV)

2SK3880

Switching Regulator Applications

- Low drain-source ON resistance: $R_{DS(ON)} = 1.35 \Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 5.2 \text{ S}$ (typ.)
- Low leakage current: $I_{DSS} = 100 \mu\text{A}$ (max) ($V_{DS} = 640 \text{ V}$)
- Enhancement model: $V_{th} = 2.0 \sim 4.0 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	800	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	800	V
Gate-source voltage		V_{GSS}	± 30	V
Drain current	DC (Note 1)	I_D	6.5	A
	Pulse (Note 1)	I_{DP}	19.5	
Drain power dissipation ($T_c = 25^\circ\text{C}$)		P_D	80	W
Single pulse avalanche energy (Note 2)		E_{AR}	375	mJ
Avalanche current		I_{AR}	6.5	A
Repetitive avalanche energy (Note 3)		E_{AR}	8	mJ
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	$-55 \sim 150$	$^\circ\text{C}$

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	1.56	$^\circ\text{C/W}$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	41.6	$^\circ\text{C/W}$

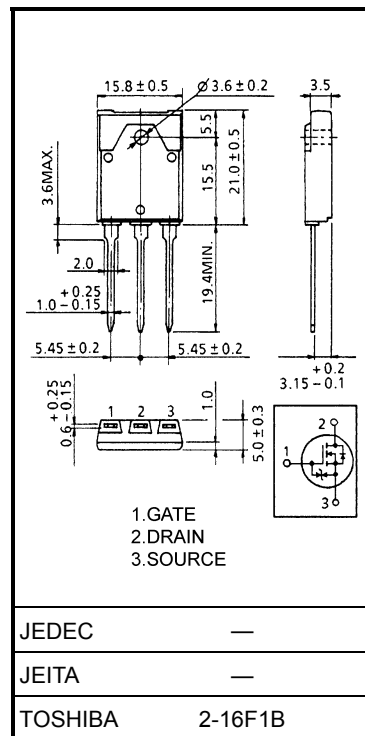
Note 1: Ensure that the channel temperature does not exceed 150°C during use of the device.

Note 2: $V_{DD} = 90 \text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 16.1 \text{ mH}$, $R_G = 25 \Omega$, $I_{AR} = 6.5 \text{ A}$

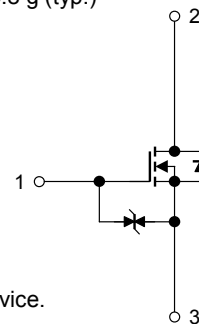
Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.

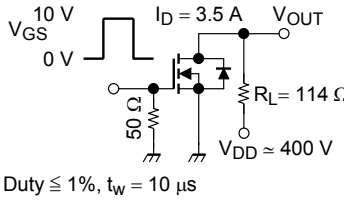
Unit: mm



Weight: 5.8 g (typ.)



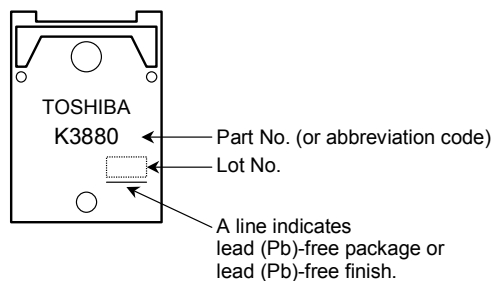
Electrical Characteristics (Ta = 25°C)

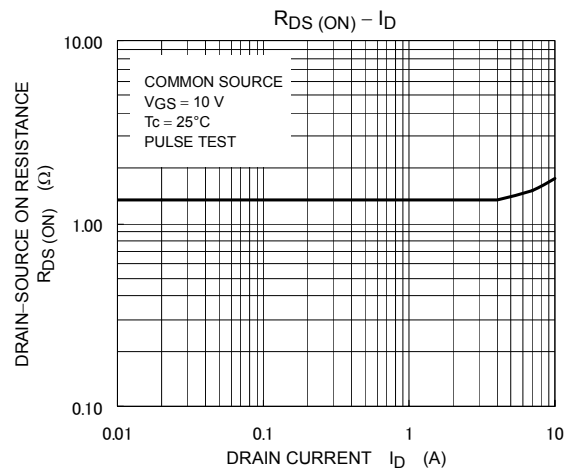
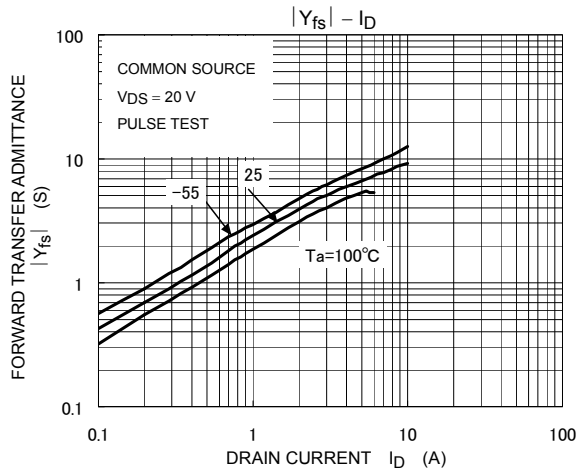
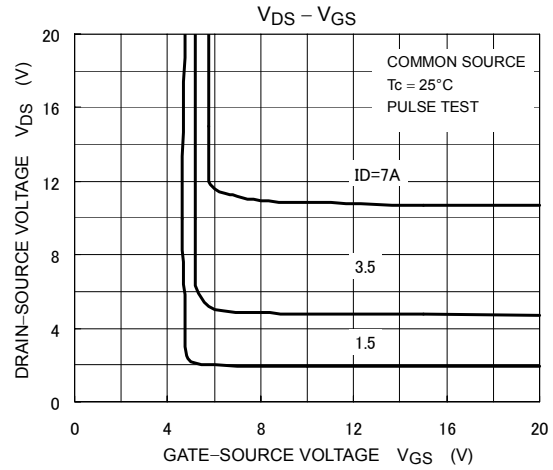
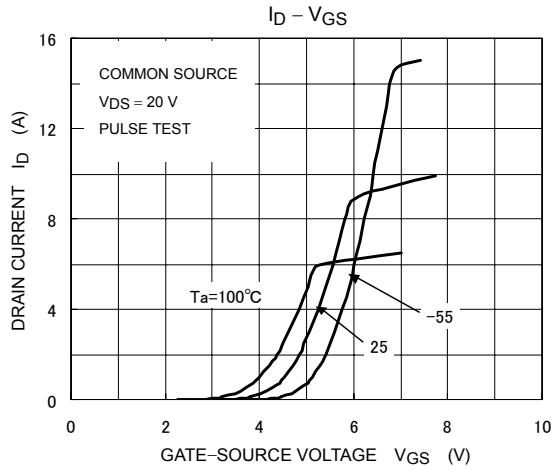
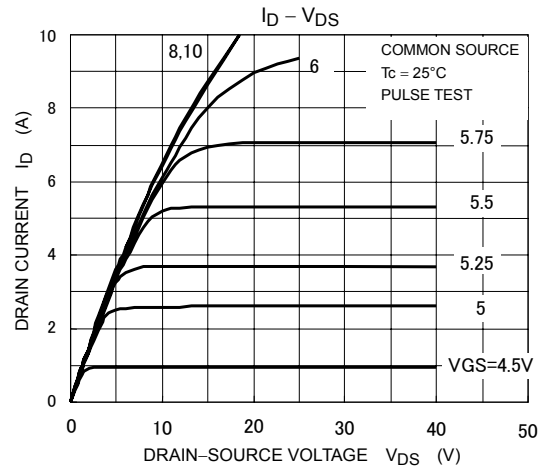
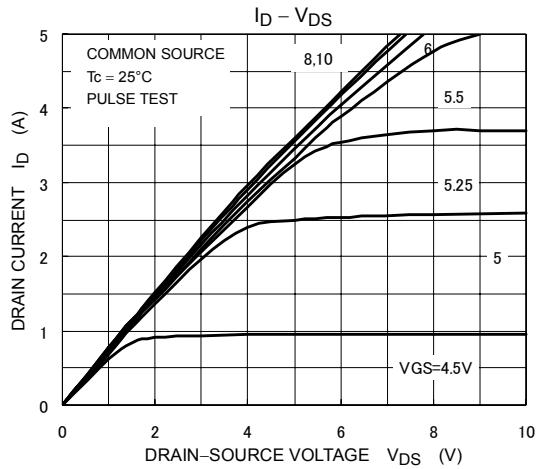
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Drain-source breakdown voltage		$V_{(BR)GSS}$	$I_G = \pm 10 \mu\text{A}, V_{DS} = 0 \text{ V}$	± 30	—	—	V
Drain cutoff current		I_{DSS}	$V_{DS} = 640 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	100	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	800	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	2.0	—	4.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}, I_D = 3.5 \text{ A}$	—	1.35	1.7	Ω
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 20 \text{ V}, I_D = 3.5 \text{ A}$	2.5	5.2	—	S
Input capacitance		C_{iss}	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	1500	—	pF
Reverse transfer capacitance		C_{rss}		—	25	—	
Output capacitance		C_{oss}		—	140	—	
Switching time	Rise time	t_r		—	35	—	ns
	Turn-on time	t_{on}		—	80	—	
	Fall time	t_f		—	50	—	
	Turn-off time	t_{off}		—	220	—	
Total gate charge (gate-source plus gate-drain)		Q_g	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 6.5 \text{ A}$	—	35	—	nC
Gate-source charge		Q_{gs}		—	22	—	
Gate-drain ("Miller") charge		Q_{gd}		—	13	—	

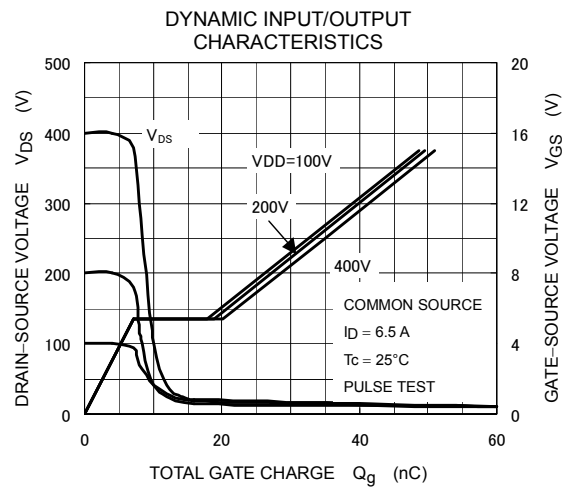
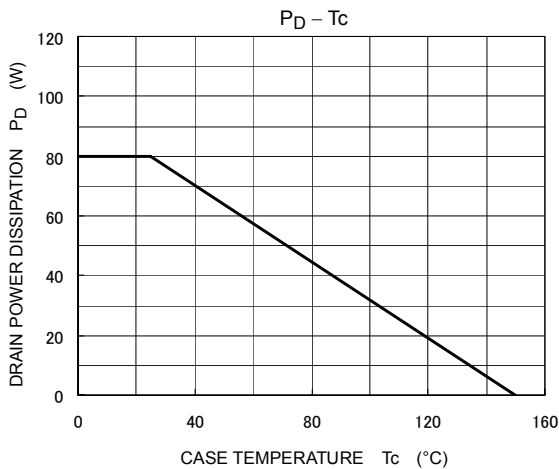
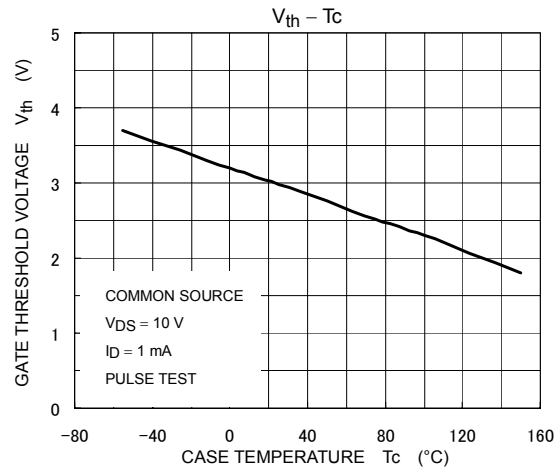
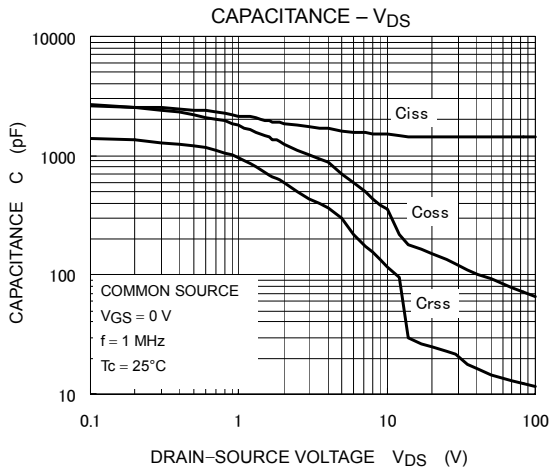
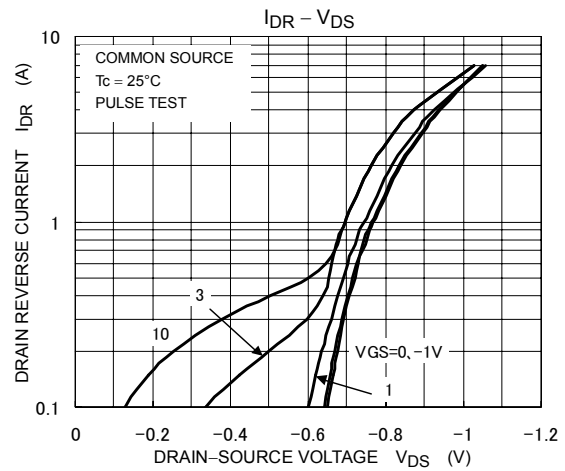
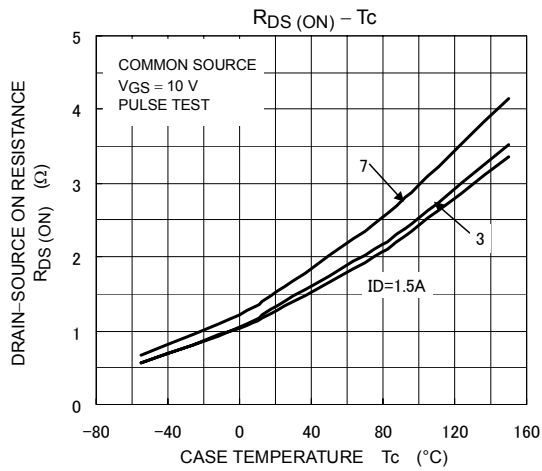
Source-Drain Ratings and Characteristics (Ta = 25°C)

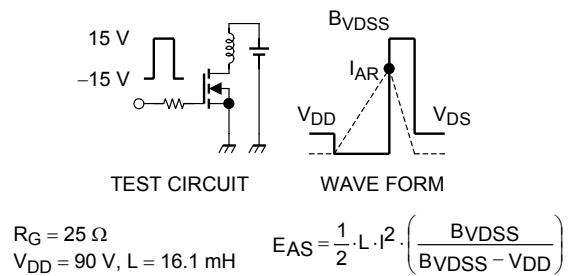
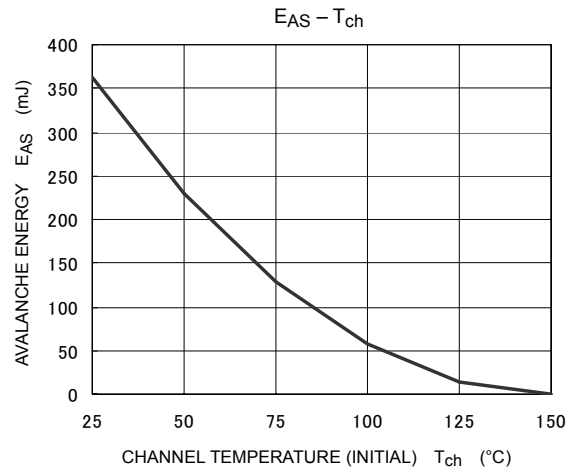
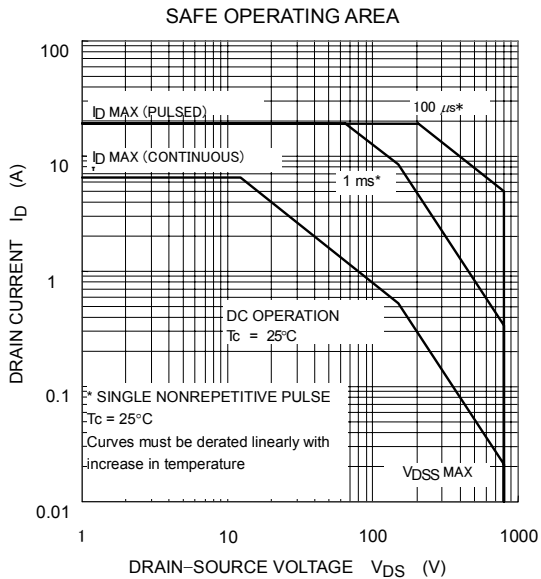
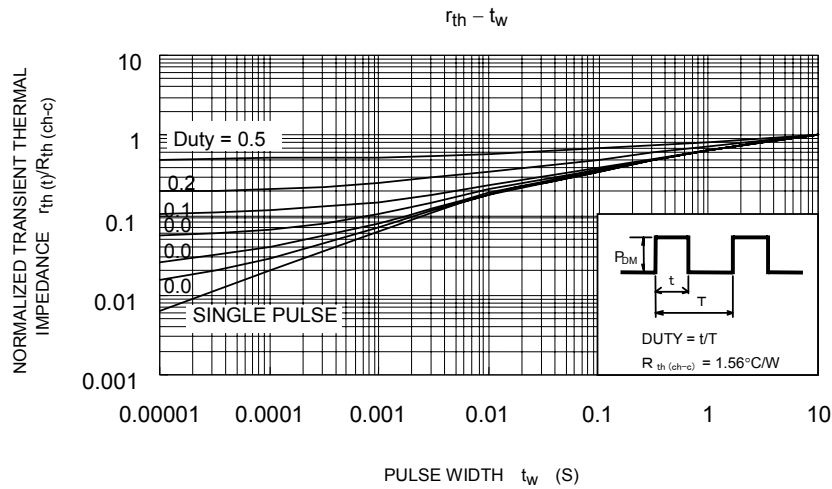
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	6.5	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	19.5	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 6.5 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.7	V
Reverse recovery time	t_{rr}	$I_{DR} = 6.5 \text{ A}, V_{GS} = 0 \text{ V},$	—	1200	—	ns
Reverse recovery charge	Q_{rr}	$dI_{DR}/dt = 100 \text{ A}/\mu\text{s}$	—	11.5	—	μC

Marking









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